L Number	Hits	Search Text	DB	Time stamp
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4	1032	@ad<=20001115 and (257/408).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:22
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7	875	@ad<=20001115 and (257/344).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:24
8	86	@ad<=20001115 and (257/e21.626).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:25
9	1368	@ad<=20001115 and (257/e21.435).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:26
10	371	@ad<=20001115 and (257/e29.278).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:26
−	3	@ad<=20011204 and 'IGFET' and 'step' near 'side wall'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 11:12
−	4231	@ad<=20011204 and 'IGFET'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 09:33
−	253	@ad<=20011204 and 'IGFET' and 'LDD'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 14:11
−	15	@ad<=20011204 and 'IGFET' and 'polycide gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:48
−	434	@ad<=20011204 and 'IGFET' and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 10:35
−	1	"4777517".PN.	USPAT	2002/07/17 10:19
−	1	"4791471".PN.	USPAT	2002/07/17 10:19

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-	1	"4889817".PN.	USPAT	2002/07/17 10:19
-	1	"4905061".PN.	USPAT	2002/07/17 10:19
-	1	"5183771".PN.	USPAT	2002/07/17 10:19
-	1	"5225286".PN.	USPAT	2002/07/17 10:19
-	1	"5243202".PN.	USPAT	2002/07/17 10:20
-	1	"5286994".PN.	USPAT	2002/07/17 10:20
-	1	"5292673".PN.	USPAT	2002/07/17 10:20
-	1	"5528068".PN.	USPAT	2002/07/17 10:20
-	1	"5596214".PN.	USPAT	2002/07/17 10:20
-	1	"5688724".PN.	USPAT	2002/07/17 10:20
-	1	"5866473".PN.	USPAT	2002/07/17 10:21
-	1	"5880508".PN.	USPAT	2002/07/17 10:21
-	1	"5891798".PN.	USPAT	2002/07/17 10:21
-	32	@ad<=20011204 and 'IGFET' and 'polysilicon gate' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:22
-	4527	((438/197-209) or (257/262) or (257/326) or (257/368) or (257/334) or (257/347)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 11:10
-	350	(438/197).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 11:12
-	13	((438/197).CCLS.) and @ad<=20011204 and 'IGFET'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 11:12
-	1554	@ad<=20001115 and (257/412-413).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:14
-	229	@ad<=20001115 and (257/388).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 09:37
-	252	@ad<=20001115 and (438/581-583).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:03
-	3446	@ad<=20001115 and (438/585-587).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 11:55
-	268	@ad<=20001115 and (438/588).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:04

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-	1179	@ad<=20001115 and (438/592).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 11:39
-	6	(("5817562") or ("6083816") or ("5731236")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 09:44
-	3	"0849777"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 09:45
-	10	"849777"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 09:45
-	2	"07183513"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 11:39
-	1005	@ad<=20001115 and (438/585).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/26 11:56
-	1603	@ad<=20001115 and (257/412-413).ccls	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:21
-	657	@ad<=20001115 and (438/585).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:21
-	1899	@ad<=20001115 and (438/586).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:22
-	245	@ad<=20001115 and (438/587).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:23
-	148	@ad<=20001115 and (438/588).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:23
-	249	@ad<=20001115 and (438/591).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:23
-	740	@ad<=20001115 and (438/592).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 08:23
-	28	@ad<=20011204 and 'IGFET' and 'silicide gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/29 09:41

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-	2	anderson-dirk.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 08:56
-	2	("6521963").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:00
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-	16	@ad<=20001115 and 'polycide' adj1 'gate' same 'etch stop'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:55
-	55	@ad<=20001115 and 'polycide' adj1 'gate' same 'LDD'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:55
-	271	@ad<=20001115 and 'polycide' adj1 'gate' and 'LDD'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:01
-	104	@ad<=20001115 and 'polycide' adj1 'gate' and 'etch stop'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:56
-	152	@ad<=20001115 and 'polycide' adj1 'gate' and 'cap'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:00
-	2	("6518636").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 07:59
-	2	("6342422").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:00
-	2	("6083816").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:01
-	2	("5654570").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:01
-	1066	@ad<=20001115 and (257/412-413).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:03
-	765	@ad<=20001115 and (257/410-411).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:04

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	153	@ad<=20001115 and (438/581-583).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 08:04
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